

MUR480EG, MUR4100EG

SWITCHMODE Power Rectifiers

Ultrafast “E” Series with High Reverse Energy Capability

These state-of-the-art devices are designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- 20 mJ Avalanche Energy Guaranteed
- Excellent Protection Against Voltage Transients in Switching Inductive Load Circuits
- Ultrafast 75 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- Low Forward Voltage
- Low Leakage Current
- High Temperature Glass Passivated Junction
- Reverse Voltage to 1000 V
- These are Pb-Free Devices*

Mechanical Characteristics:

- Case: Epoxy, Molded
- Weight: 1.1 Gram (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped in Plastic Bags, 5,000 per Bag
- Available Tape and Reel, 1,500 per Reel, by Adding a “RL” Suffix to the Part Number
- Polarity: Cathode indicated by Polarity Band

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|---------------------------------|-----------------------------------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MUR480E MUR4100E | V_{RRM} V_{RWM} V_R | 800 1000 | V |
| Average Rectified Forward Current (Square Wave; Mounting Method #3 Per Note 2) | $I_{F(AV)}$ | 4.0 @ $T_A = 35^\circ\text{C}$ | A |
| Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz) | I_{FSM} | 70 | A |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | -65 to +175 | °C |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



ON Semiconductor®

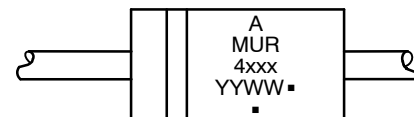
<http://onsemi.com>

ULTRAFAST RECTIFIER 4.0 AMPERES, 800–1000 VOLTS



AXIAL LEAD
CASE 267
STYLE 1

MARKING DIAGRAM



A = Assembly Location
MUR4xxx = Device Number (see page 2)
YY = Year
WW = Work Week
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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THERMAL CHARACTERISTICS

| Rating | Symbol | Value | Unit |
|---|-----------------|------------|-----------------------------|
| Maximum Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | See Note 2 | $^{\circ}\text{C}/\text{W}$ |

ELECTRICAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|--|-------------|----------------------|---------------|
| Maximum Instantaneous Forward Voltage (Note 1) ($I_F = 3.0\text{ A}$, $T_J = 150^{\circ}\text{C}$) ($I_F = 3.0\text{ A}$, $T_J = 25^{\circ}\text{C}$) ($I_F = 4.0\text{ A}$, $T_J = 25^{\circ}\text{C}$) | V_F | 1.53 1.75 1.85 | V |
| Maximum Instantaneous Reverse Current (Note 1) (Rated dc Voltage, $T_J = 150^{\circ}\text{C}$) (Rated dc Voltage, $T_J = 25^{\circ}\text{C}$) | I_R | 900 25 | μA |
| Maximum Reverse Recovery Time ($I_F = 1.0\text{ Amp}$, $di/dt = 50\text{ Amp}/\mu\text{s}$) ($I_F = 0.5\text{ Amp}$, $I_R = 1.0\text{ Amp}$, $I_{REC} = 0.25\text{ Amp}$) | t_{rr} | 100 75 | ns |
| Maximum Forward Recovery Time ($I_F = 1.0\text{ Amp}$, $di/dt = 100\text{ Amp}/\mu\text{s}$, Recovery to 1.0 V) | t_{fr} | 75 | ns |
| Controlled Avalanche Energy (See Test Circuit in Figure 6) | W_{AVAIL} | 20 | mJ |
| Typical Peak Reverse Recovery Current ($I_F = 1.0\text{ A}$, $di/dt = 50\text{ A}/\mu\text{s}$) | I_{RM} | 2 | A |

1. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

| Device | Marking | Package | Shipping [†] |
|-------------|----------|-------------|-----------------------|
| MUR480E | MUR480E | Axial Lead* | 500 Units / Bulk |
| MUR480EG | | Axial Lead* | 500 Units / Bulk |
| MUR480ERL | | Axial Lead* | 1500 / Tape & Reel |
| MUR480ERLG | | Axial Lead* | 1500 / Tape & Reel |
| MUR480ES | MUR480ES | Axial Lead* | 500 Units / Bulk |
| MUR480ESG | | Axial Lead* | 500 Units / Bulk |
| MUR4100E | MUR4100E | Axial Lead* | 500 Units / Bulk |
| MUR4100EG | | Axial Lead* | 500 Units / Bulk |
| MUR4100ERL | | Axial Lead* | 1500 / Tape & Reel |
| MUR4100ERLG | | Axial Lead* | 1500 / Tape & Reel |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*This package is inherently Pb-Free.

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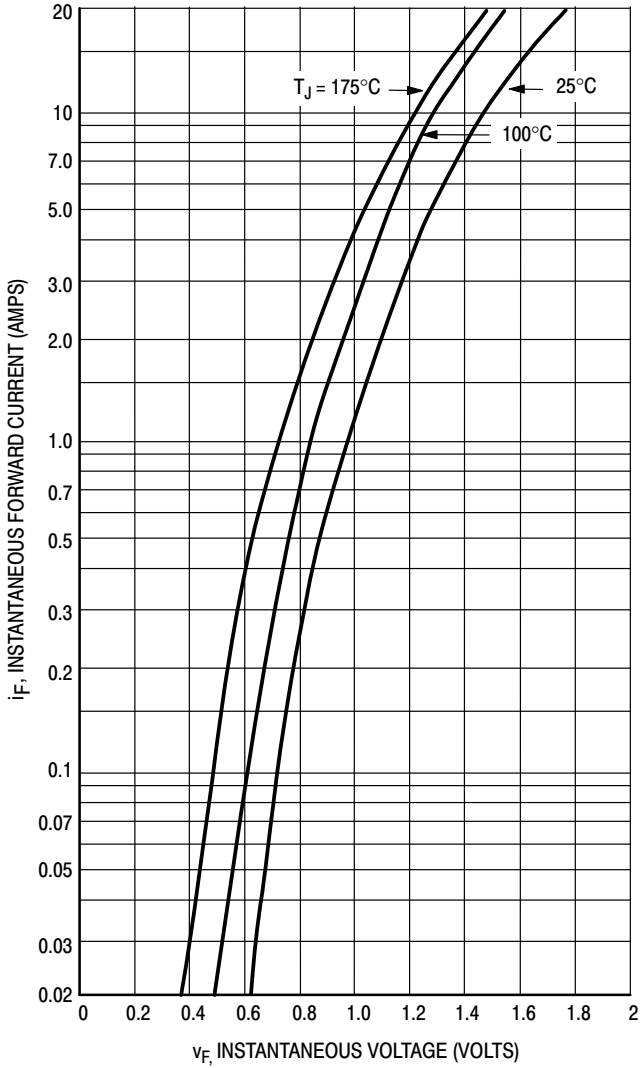


Figure 1. Typical Forward Voltage

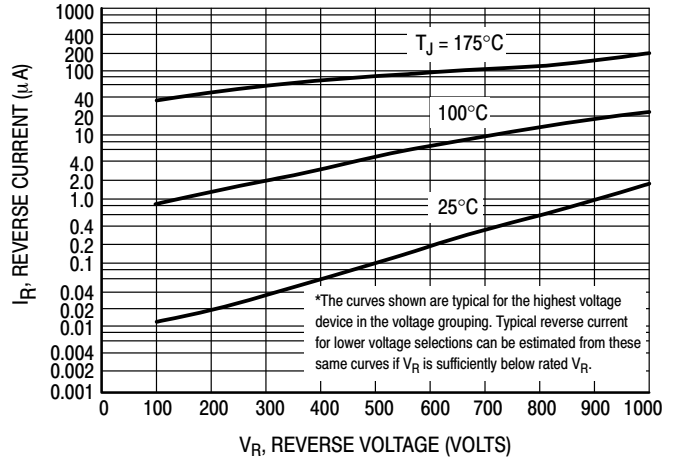


Figure 2. Typical Reverse Current*

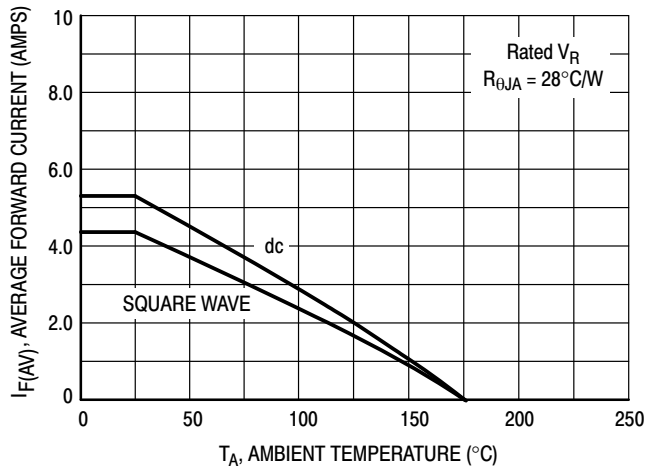


Figure 3. Current Derating (Mounting Method #3 Per Note 2)

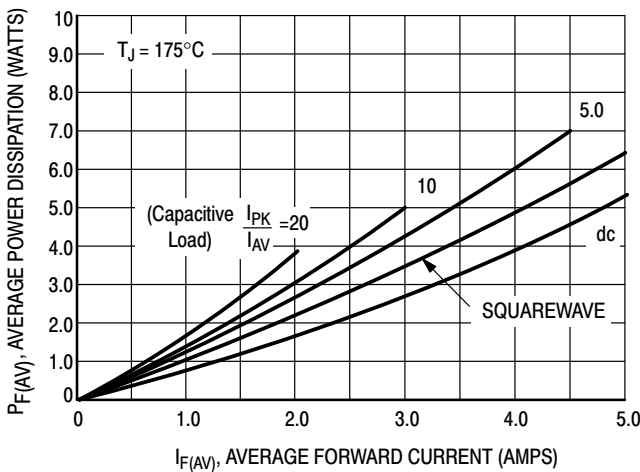


Figure 4. Power Dissipation

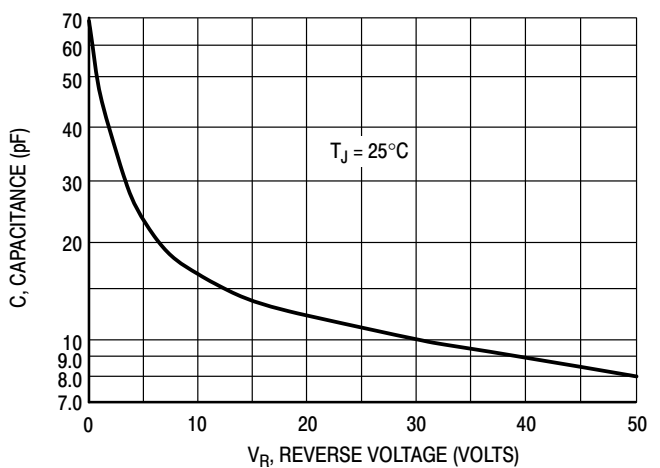


Figure 5. Typical Capacitance

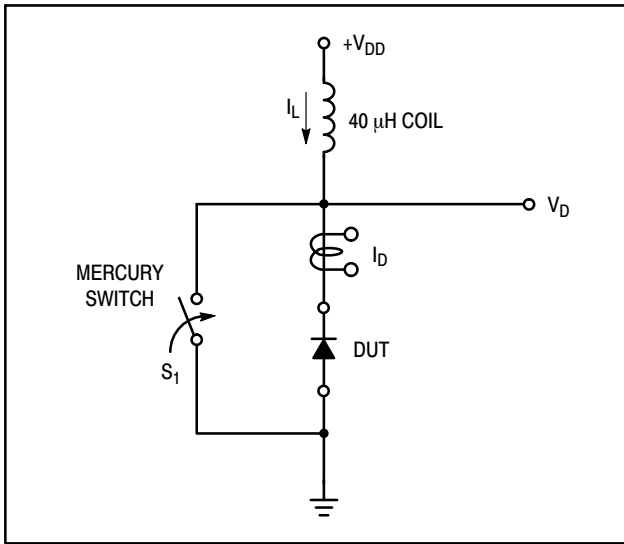


Figure 6. Test Circuit

The unclamped inductive switching circuit shown in Figure 6 was used to demonstrate the controlled avalanche capability of the new “E” series Ultrafast rectifiers. A mercury switch was used instead of an electronic switch to simulate a noisy environment when the switch was being opened.

When S₁ is closed at t₀ the current in the inductor I_L ramps up linearly; and energy is stored in the coil. At t₁ the switch is opened and the voltage across the diode under test begins to rise rapidly, due to di/dt effects, when this induced voltage reaches the breakdown voltage of the diode, it is clamped at BV_{DUT} and the diode begins to conduct the full load current which now starts to decay linearly through the diode, and goes to zero at t₂.

By solving the loop equation at the point in time when S₁ is opened; and calculating the energy that is transferred to the diode it can be shown that the total energy transferred is equal to the energy stored in the inductor plus a finite amount of energy from the V_{DD} power supply while the diode is in breakdown (from t₁ to t₂) minus any losses due to finite

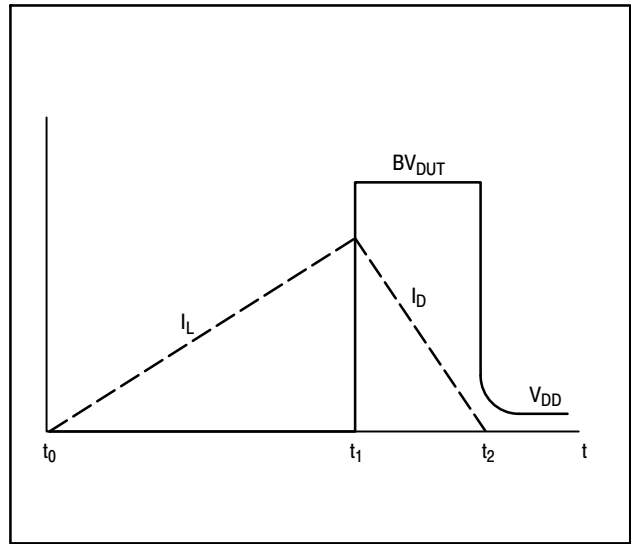


Figure 7. Current–Voltage Waveforms

component resistances. Assuming the component resistive elements are small Equation (1) approximates the total energy transferred to the diode. It can be seen from this equation that if the V_{DD} voltage is low compared to the breakdown voltage of the device, the amount of energy contributed by the supply during breakdown is small and the total energy can be assumed to be nearly equal to the energy stored in the coil during the time when S₁ was closed, Equation (2).

The oscilloscope picture in Figure 8, shows the information obtained for the MUR8100E (similar die construction as the MUR4100E Series) in this test circuit conducting a peak current of one ampere at a breakdown voltage of 1300 V, and using Equation (2) the energy absorbed by the MUR8100E is approximately 20 mjoules.

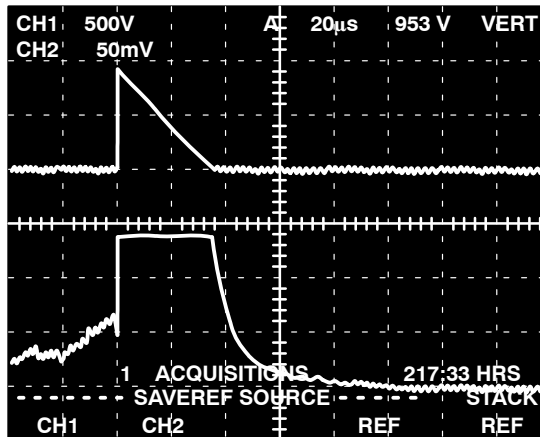
Although it is not recommended to design for this condition, the new “E” series provides added protection against those unforeseen transient viruses that can produce unexplained random failures in unfriendly environments.

EQUATION (1):

$$W_{\text{AVAL}} \approx \frac{1}{2} L I_{\text{LPK}}^2 \left(\frac{BV_{\text{DUT}}}{BV_{\text{DUT}} - V_{\text{DD}}} \right)$$

EQUATION (2):

$$W_{\text{AVAL}} \approx \frac{1}{2} L I_{\text{LPK}}^2$$



CHANNEL 2:

I_L
0.5 AMPS/DIV.

CHANNEL 1:

V_{DUT}
500 VOLTS/DIV.

TIME BASE:

20 μs/DIV.

Figure 8. Current–Voltage Waveforms

MUR480EG, MUR4100EG

NOTE 2 – AMBIENT MOUNTING DATA

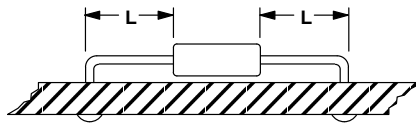
Data shown for thermal resistance junction-to-ambient ($R_{\theta JA}$) for the mountings shown is to be used as typical guideline values for preliminary engineering or in case the tie point temperature cannot be measured.

TYPICAL VALUES FOR $R_{\theta JA}$ IN STILL AIR

| Mounting Method | $R_{\theta JA}$ | Lead Length, L (IN) | | | | Units |
|-----------------|-----------------|---------------------|-----|-----|-----|-----------------------------|
| | | 1/8 | 1/4 | 1/2 | 3/4 | |
| 1 | | 50 | 51 | 53 | 55 | $^{\circ}\text{C}/\text{W}$ |
| 2 | | 58 | 59 | 61 | 63 | $^{\circ}\text{C}/\text{W}$ |
| 3 | | 28 | | | | $^{\circ}\text{C}/\text{W}$ |

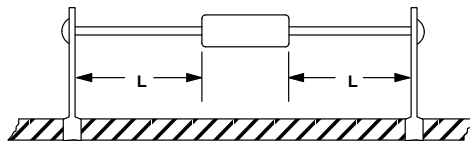
MOUNTING METHOD 1

P.C. Board Where Available Copper Surface area is small.



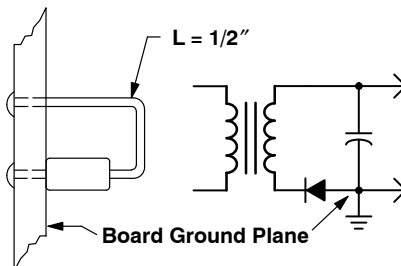
MOUNTING METHOD 2

Vector Push-In Terminals T-28



MOUNTING METHOD 3

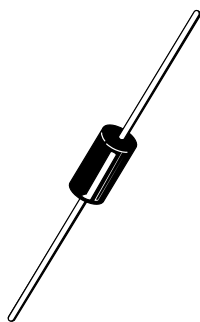
P.C. Board with
1-1/2" x 1-1/2" Copper Surface



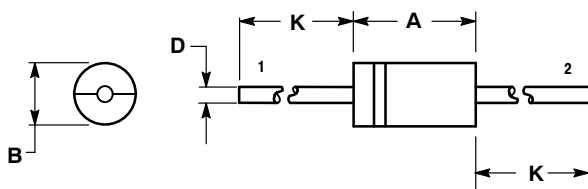


AXIAL LEAD
CASE 267-05
ISSUE G

DATE 06/06/2000



SCALE 1:1



- NOTES:
1. DIMENSIONS AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. 267-04 OBSOLETE, NEW STANDARD 267-05.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|------|
| | MIN | MAX | MIN | MAX |
| A | 0.287 | 0.374 | 7.30 | 9.50 |
| B | 0.189 | 0.209 | 4.80 | 5.30 |
| D | 0.047 | 0.051 | 1.20 | 1.30 |
| K | 1.000 | --- | 25.40 | --- |

STYLE 1:
 PIN 1. CATHODE (POLARITY BAND)
 2. ANODE

STYLE 2:
 NO POLARITY

| | | |
|-------------------------|--------------------|--|
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